

# Dual Wavelength InGaAs Avalanche Photodiode Preamplifier Module

HIGH SENSITIVITY . LOW NOISE . MULTI USE

A distance detecting device should provide you with accurate and consistent readings under a variety of conditions and wavelengths. Whether you are dealing with low signals or high, warm weather or cold, distances near or far, your decision making depends on the speed and precision of the information you receive.

CMC's new *InGaAs Avalanche Photodiode (APD) Preamplifier Module* supports designs that detect farther distances more accurately than other device of its kind. Plus, it is safe and practical, operating guietly and efficiently in multiple scenarios.

#### Fast, accurate and practical all rolled into one receiver

- High-density microcircuit combined with advanced optoelectronics
- · Nanosecond recovery from laser bursts without damage
- Ability to detect signal power in low nW
- · Low NEP at high temperatures
- Compact design minimizing parasitic noise

#### CMC is committed to:

264-339822

- Work closely with your engineering team throughout the project
- · Develop a solution that is tailored to your design needs
- Take the time required to deliver a quality product

### FEATURES

**One receiver, two wavelengths** This eye-safe receiver works at both 1064 nm and 1570 nm

#### Sensitive for ultra low light signals

Detects longer distances more quickly, accurately, and consistently

#### Fast overload recovery

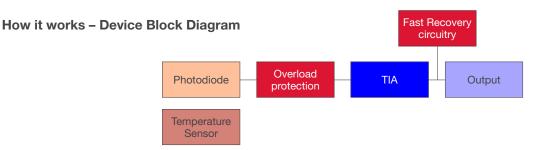
Minimizes receiver damage and usage interruption from high laser bursts

#### **KEY APPLICATIONS**

- Eye-safe laser range finding
- Airborne Lidar
- High-speed low-light level detection
- Industrial, medical, analytical and defense applications
- Well suited for high-volume applications and when you have your own temperature compensation circuit



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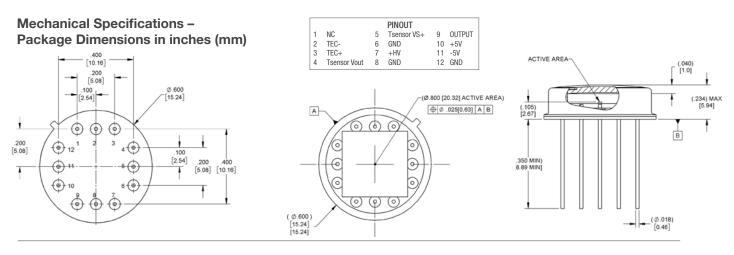


## Electro-Optical Characteristics at T<sub>A</sub> = 25°C

Unless otherwise specified: V+=5V, V-=-5V, V<sub>R</sub>, R<sub>L</sub>=100Ω AC, cooler OFF (Externally AC coupled through 4.7 μF)

Parameter/Condition	Min.	Тур.	Max.	Unit
Active area		200		μm
V <sub>R</sub> for specified responsivity	40	NOTE <sup>1</sup>	85	V
Temperature coefficient of V <sub>R</sub>	-	0.080	-	V/°C
ADP dark current (ld) @ 22 °C	-	20	50	nA
Responsivity (R) 1570 nm, M = 10	-	580	-	kV/W
Noise equivalent power (NEP = E <sub>n</sub> /R)				
Wavelength = 1570 nm [Tcase = 25 °C]	-	110	135	fW/√Hz
[Tcase = 85 °C]	-	255	525	fW/√Hz
Output impedance	-	10	-	Ω
Bandwidth = $f_{-3dB}$	50	60	100	MHz
Rise time (10-90%)	-	6	-	ns
Fall time = $t_F$ (90-10%)	-	6	-	ns
Linear output voltage swing (Pulse)	1.5	2.5	4.0	V
Output offset voltage	-0.75	-0.45	0	V
Temperature sensor (1N914 diode)				
with bias current = 5mA	-	700	-	mV
Overload recovery for optical power input signal of 1mW				
20 µs pulse width:				
$V_{out} - V_{out PrePulse} \rightarrow 200 \ \mu s \ after \ pulse \ start$	-	-	250	mV
$V_{out} - V_{out PrePulse} \rightarrow 1 \ \mu s$ after pulse start	-	-	40	mV
Hybrid Supply Current V_POS (pin 12)	25	-	35	mA
V_NEG (pin 3)	-20	-	-10	mA

 $NOTE^{1}V_{B}$  as specified on test data supplied with each module



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